

Switching diode

• Applications

High speed switching

• Features

- 1) Extremely small surface mounting type.
- 2) High Speed.
- 3) High reliability.

• Construction

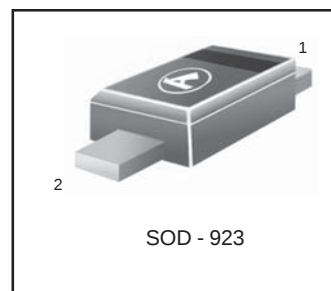
Silicon epitaxial planar

- We declare that the material of product compliance with RoHS requirements.

• Device Marking

L1SS400CST1G=3

L1SS400CST1G



ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	90	V
DC reverse voltage	V_R	80	V
Peak forward current	I_{FM}	225	mA
Mean rectifying current	I_O	100	mA
Surge current (1s)	I_{surge}	500	mA
Junction temperature	T_J	125	°C
Storage temperature	T_{stg}	- 55 ~ +125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	1.2	V	$I_F=100mA$
Reverse current	I_R	—	—	0.1	μA	$V_R=80V$
Capacitance between terminals	C_T	—	0.72	3.0	pF	$V_R=0.5V$, $f=1MHz$
Reverse recovery time	t_{rr}	—	—	4	n	$V_R=6V$, $I_F=10mA$, $R_L=100\Omega$

ORDRING INFORMATION

Device	Marking	Shipping
L1SS400CST1G	3	3000/Tape&Reel
L1SS400CST3G	3	10000/Tape&Reel

L1SS400CST1G

ELECTRICAL CHARACTERISTIC CURVES

($T_a = 25^\circ\text{C}$)

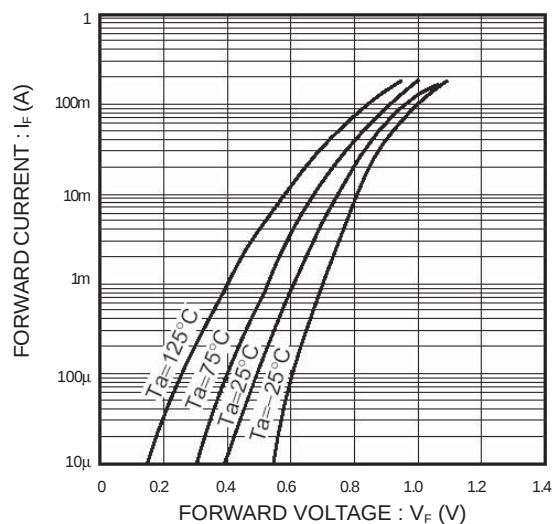


Fig.1 Forward characteristics

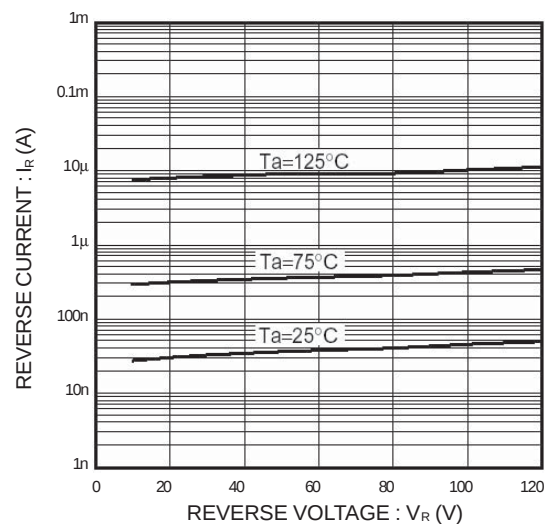


Fig.2 Reverse characteristics

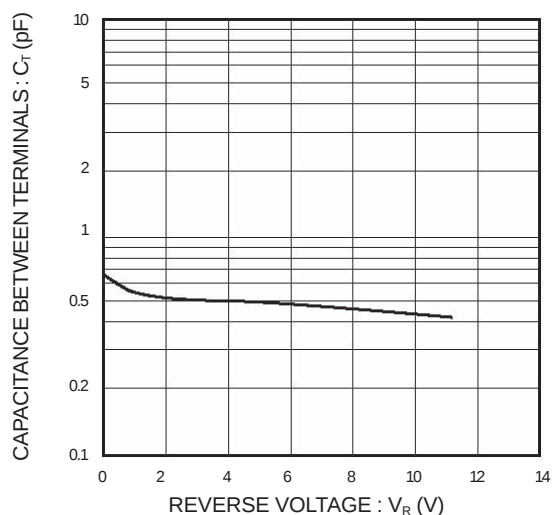


Fig.3 Capacitance between terminals

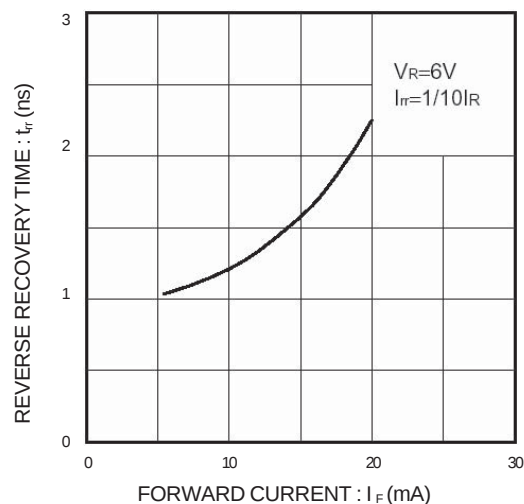


Fig.4 Reverse recovery time characteristics

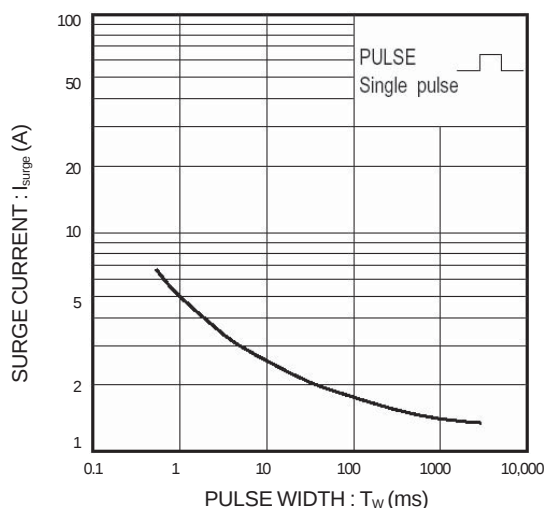


Fig.5 Surge current characteristics

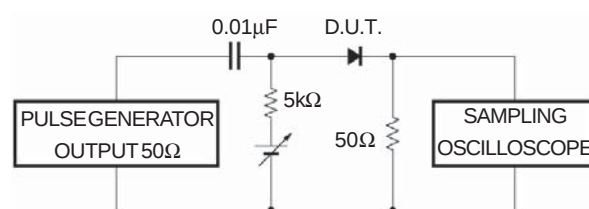
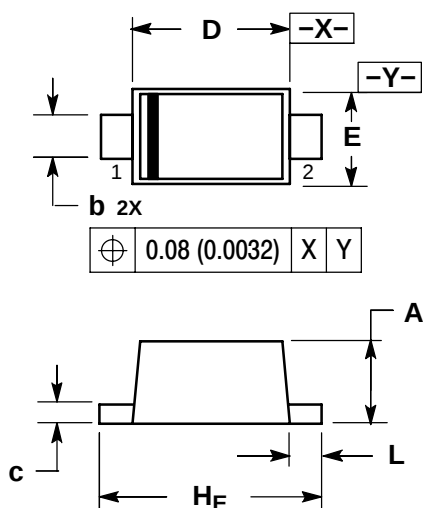


Fig.6 Reverse recovery time (t_{rr}) measurement circuit

L1SS400CST1G
SOD-923


DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.39	0.43	0.013	0.015	0.017
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
H _E	0.95	1.00	1.05	0.037	0.039	0.041
L	0.05	0.10	0.15	0.002	0.004	0.006

SOLDERING FOOTPRINT*
